Abstracts

Rectification Failure in GaAs MESFETs Subjected to Single Pulses of Intense Microwave Radiation

J.H. McAdoo, W.M. Bollen, R. Seeley, W. Catoe and J. Frey. "Rectification Failure in GaAs MESFETs Subjected to Single Pulses of Intense Microwave Radiation." 1990 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 90.1 (1990 [MCS]): 47-49.

An important mechanism for damage to GaAs microwave integrated circuits from single pulses of intense microwave radiation has been observed by the use of high speed photography, and optical spectroscopy and rf spectroscopy. We call this mechanism rectification failure because it transforms the Schottky junctions of the transistors to ohmic resistors.

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